

June 2014

# **FDB016N04AL7**

# N-Channel PowerTrench<sup>®</sup> MOSFET 40 V, 306 A, 1.6 m $\Omega$

#### **Features**

- $R_{DS(on)}$  = 1.16 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 80 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low  $R_{\mbox{\footnotesize{DS(on)}}}$
- · High Power and Current Handling Capability
- · RoHS Compliant

#### **Description**

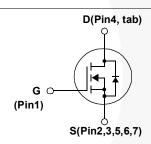
This N-Channel MOSFET is produced using Fairchild Semiconductor's advance PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

#### **Applications**

- Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- Motor drives and Uninterruptible Power Supplies



1. Gate
2. Source
3. Source
4. Drain
5. Source
6. Source
7. Source



## **MOSFET Maximum Ratings** T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter	FDB016N04AL7	Unit
$V_{DSS}$	Drain to Source Voltage		40	V
V <sub>GSS</sub>	Gate to Source Voltage		±20	V
1		- Continuous (T <sub>C</sub> = 25°C, Silicon Limited)	306*	
D	Drain Current	- Continuous (T <sub>C</sub> = 100°C, Silicon Limited)	216*	Α
		- Continuous (T <sub>C</sub> = 25°C, Package Limited)	160	
DM	Drain Current	- Pulsed (Note 1)	1224	Α
- AS	Single Pulsed Avalanche	Energy (Note 2)	1350	mJ
dv/dt	Peak Diode Recovery dv/d	dt (Note 3)	6.0	V/ns
<b>n</b>	Power Dissipation	(T <sub>C</sub> = 25°C)	283	W
D	Power Dissipation	- Derate Above 25°C	1.89	W/°C
Γ <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Te	mperature Range	-55 to +175	°C
Γ <sub>L</sub>	Maximum Lead Temperat 1/8" from Case for 5 Seco	300	°C	

<sup>\*</sup>Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 160 A.

#### **Thermal Characteristics**

Symbol	Parameter FDB016N04AL7		Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.53	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 62.5		C/VV

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDB016N04AL7	FDB016N04A	D2PAK-7L	Tape and Reel	330 mm	24 mm	800 units

# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	lest Conditions	win.	ıyp.	wax.	Unit
Off Chara	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ} C$	40	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C	-	0.03	-	V/°C
1	Zero Gate Voltage Drain Current	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	10	μА
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 32 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μΑ
I <sub>GSS</sub>	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

#### On Characteristics

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1.0	-	3.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 80 A	-	1.16	1.6	mΩ
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 80 \text{ A}$	-	381	-	S

## **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V = 25 V V = 0 V		-	8715	11600	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz		-	2035	2710	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 – 1 101112		-\	230	-	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V			- \	129	167	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	$V_{DS} = 32 \text{ V}, I_{D} = 80 \text{ A},$		-	28	-	nC
Q <sub>gs2</sub>	Gate Charge Threshold to Plateau	$V_{GS}$ = 10 V		-	12	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge	(Note	4)	-	17	-	nC

#### **Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time		-	21	52	ns
t <sub>r</sub>		$V_{DD} = 20 \text{ V}, I_{D} = 80 \text{ A},$	-	14	38	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$R_G = 4.7 \Omega, V_{GS} = 10 V$	-	118	246	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	- //	33	76	ns
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	- /	1.25	-	Ω

#### **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Dio	Maximum Continuous Drain to Source Diode Forward Current		-	306	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	1224	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 80 A	-	-	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 80 A,	-	68	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> /dt = 100 A/μs	-	84	-	nC

#### Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 3 mH, I<sub>AS</sub> = 30 A, V<sub>DD</sub> = 25 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C.
- 3. I  $_{SD} \leq$  80 A, di/dt  $\leq$  200 A/µs, V  $_{DD} \leq$  BV  $_{DSS},$  starting T  $_{J}$  = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

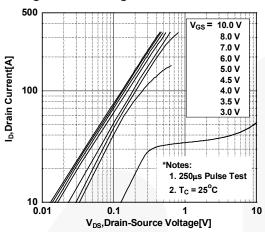


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

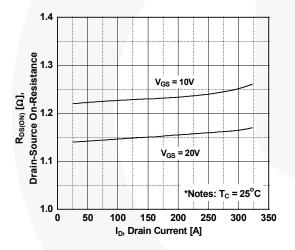


Figure 5. Capacitance Characteristics

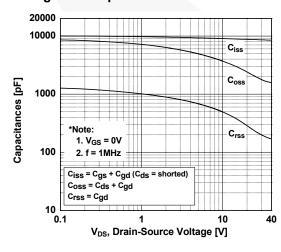


Figure 2. Transfer Characteristics

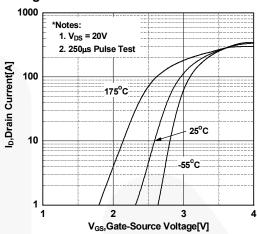


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

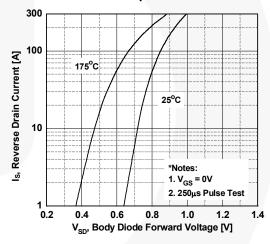
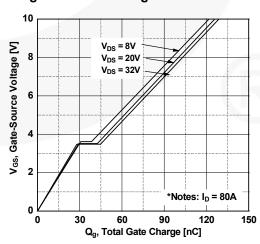


Figure 6. Gate Charge Characteristics



#### Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

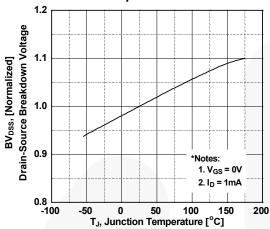


Figure 9. Maximum Safe Operating Area

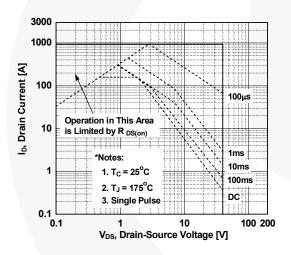


Figure 11. Unclamped Inductive Switching Capability

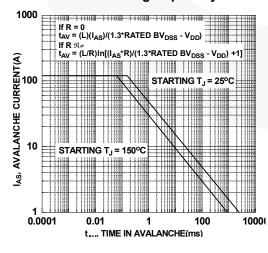


Figure 8. On-Resistance Variation vs. Temperature

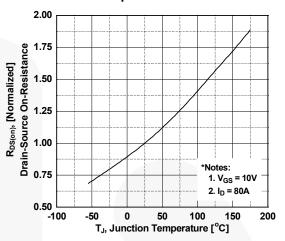
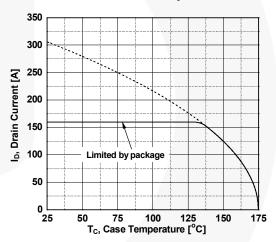


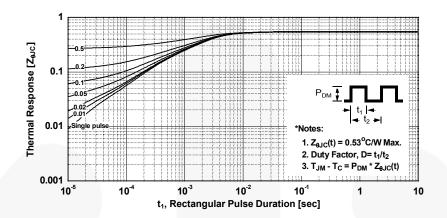
Figure 10. Maximum Drain Current vs.

Case Temperature



# **Typical Performance Characteristics** (Continued)

**Figure 12. Transient Thermal Response Curve** 



5

Figure 13. Gate Charge Test Circuit & Waveform

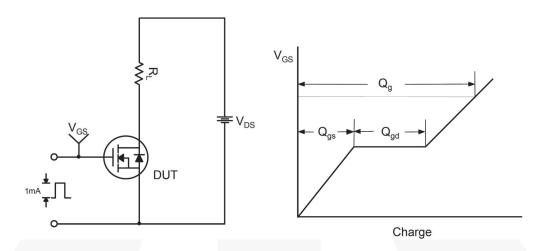


Figure 14. Resistive Switching Test Circuit & Waveforms

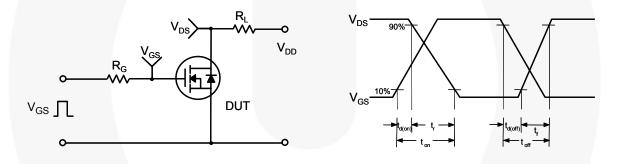
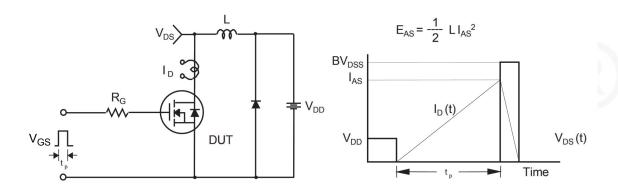
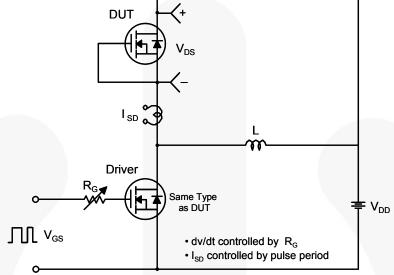


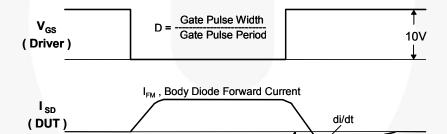
Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

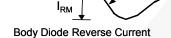


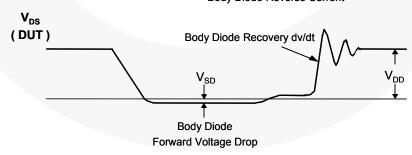
DUT

Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms









#### **Mechanical Dimensions**

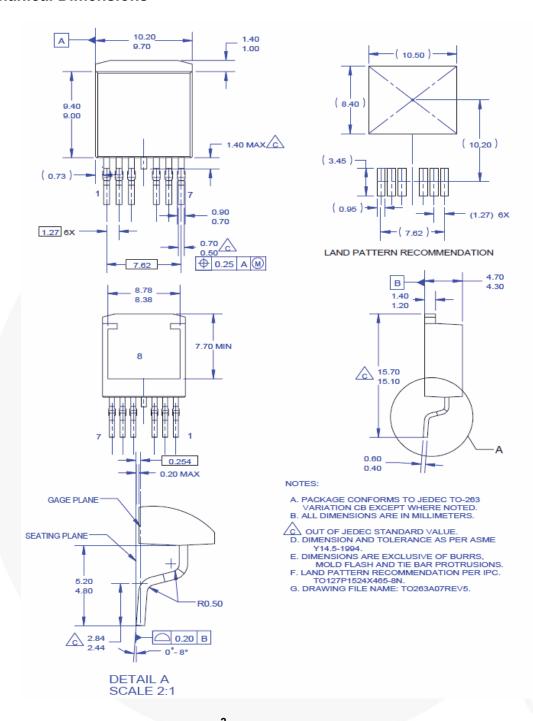


Figure 17. TO263 (D<sup>2</sup>PAK), Molded, 7-Lead, Surface Mount

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Rev. 168

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